

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) An active-matrix substrate comprising:

a substrate;

a signal line;

a scanning line;

a switching element; and

a pixel electrode,

the signal line and the scanning line forming a lattice on the substrate, and the switching element and the pixel electrode being provided for each unit lattice of the signal line and the scanning line,

the pixel electrode not overlapping the signal line and the scanning line, and satisfying a relation $X1 > Y1$, where $X1$ is a gap between the pixel electrode and the signal line, and $Y1$ is a gap between the pixel electrode and the scanning line, and wherein $X1 > Y1$ is satisfied on both first and second opposing sides of the pixel electrode which are adjacent to first and second respective signal lines.

2. (Original) The active-matrix substrate as set forth in claim 1, further comprising:

a capacitor, provided for each unit lattice, having a capacitor electrode made from a metal film,

wherein the capacitor electrode does not overlap the signal line and the scanning line, and satisfies a relation $X2 > Y2$, where $X2$ is a gap between the capacitor electrode and the signal line, and $Y2$ is a gap between the capacitor electrode and the scanning line.

3. (Original) An electromagnetic wave detector comprising:

an active-matrix substrate;

a semiconductor film, disposed on the active-matrix substrate, for generating charge in response to an electromagnetic wave being imaged; and

a pixel electrode, disposed on the active-matrix substrate, serving as an electrode for collecting generated charge in the semiconductor film,

the active-matrix substrate including:

a substrate;

a signal line;

a scanning line;

a switching element; and

a pixel electrode,

the signal line and the scanning line forming a lattice on the substrate, and the switching element and the pixel electrode being provided for each unit lattice of the signal line and the scanning line, and

the pixel electrode not overlapping the signal line and the scanning line, and satisfying a relation $X1 > Y1$, where $X1$ is a gap between the pixel electrode and the signal line, and $Y1$ is a gap between the pixel electrode and the scanning line.

4. (Original) The electromagnetic wave detector as set forth in claim 3, further comprising:

a light source on a back of the active-matrix substrate on which the pixel electrode is formed.

5. (Original) The electromagnetic wave detector as set forth in claim 4, wherein:

the active-matrix substrate includes a pixel capacitor that is provided for each unit lattice and having a capacitor electrode made from a metal film; and

the capacitor electrode does not overlap the signal line and the scanning line, and satisfies a relation $X2 > Y2$, where $X2$ is a gap between the capacitor electrode and the signal line, and $Y2$ is a gap between the capacitor electrode and the scanning line.

6. (New) The active matrix substrate of claim 1, wherein the pixel electrode is a charge collecting electrode, and the active matrix substrate is part of an electromagnetic wave detector.

7. (New) The active matrix substrate of claim 1, wherein the active matrix substrate is part of an electromagnetic wave detector that includes a semiconductor film for generating charge in response to an electromagnetic wave being imaged.

8. (New) The electromagnetic wave detector of claim 3, wherein $X1 > Y1$ is satisfied on both first and second opposing sides of the pixel electrode which are adjacent to first and second respective signal lines.